N on linear transm ission and light localization in photonic crystal waveguides

Sergei F.M ingaleev and Yuri S.K ivshar

N onlinear Physics G roup, Research School of Physical Sciences and Engineering Australian National University, Canberra ACT 0200, Australia

W e study the light transm ission in two-dim ensional photonic crystal waveguides with embedded nonlinear defects. First, we derive the e ective discrete equations with long-range interaction for describing the waveguide m odes, and dem onstrate that they provide a highly accurate generalization of the familiar tight-binding m odels which are employed, e.g., for the study of the coupledresonator optical waveguides. U sing these equations, we investigate the properties of straight waveguides and waveguide bends with embedded nonlinear defects and dem onstrate the possibility of the nonlinearity-induced bistable transm ission. A dditionally, we study localized m odes in the waveguide bends and (linear and nonlinear) transm ission of the bent waveguides and emphasize the role of evanescent m odes in these phenom ena.

1. Introduction

Photonic crystals are usually viewed as an optical analog of sem iconductors that modify the properties of light sim ilar to a microscopic atom ic lattice that creates a sem iconductor band-gap for electrons¹. One of the most prom ising applications of photonic crystals is a possibility to create compact integrated optical devices², which would be analogous to the integrated circuits in electronics, but operating entirely with light. Replacing relatively slow electrons with photons as the carriers of inform ation, the speed and bandwidth of advanced com – munication systems can be dram atically increased, thus revolutionizing the telecommunication industry.

To employ the high-tech potential of photonic crystals for optical applications and all-optical switching and waveguiding technologies, it is crucially important to achieve a dynamical tunability of their properties. For this purpose, several approaches have been suggested (see, e.g., Ref. 3). One of the most prom ising concepts is based on the idea to employ the properties of nonlinear photonic crystals, i.e. photonic crystals made from dielectric materials whose refractive index depends on the light intensity. Exploration of nonlinear properties of photonic band-gap m aterials is an important direction of current research that opens a broad range of novel applications of photonic crystals for all-optical signal processing and switching, allowing an e ective way to create highly tunable band-gap structures operating entirely with light.

O ne of the important concepts in the physics of photonic crystals is related to the eld localization on defects. In the solid-state physics, the idea of localization is associated with disorder that breaks the translational

invariance of a crystal lattice and supports spatially localized modes with the frequency outside the phonon bands. The sim ilar concept is well-known in the physics of photonic crystals where an isolated defect (a region with di erent refractive index which breaks periodicity) is known to support a localized defect mode. An array of such defects creates a waveguide that allows a directed light transm ission for the frequencies inside the band gap. Since the frequencies of the defect modes created by nonlinear defects depend on the electric eld intensity, such modes can be useful to control the light transmission. From the view point of possible practical applications, spatially localized states in optics can be associated with di erent types of all-optical switching devices where light manipulates and controls light itself due to the varying input intensity.

N onlinearphotonic crystals and photonic crystals with embedded nonlinear defects create an ideal environm ent for the observation of many of the nonlinear elects earlier predicted and studied in other branches of physics. In particular, the existence of nonlinear localized modes with the frequencies in the photonic band gaps has already been predicted and demonstrated numerically for several models of photonic crystals with the Kerr-type nonlinearity⁴^{{6}</sup>.

In this paper, we study the resonant light transm ission and localization in the photonic crystal waveguides and bends with embedded nonlinear defects. For sim plicity, we consider the case of a photonic crystal created by a square lattice of in nite dielectric rods, with waveguides made by removing some of the rods. Nonlinear properties of the waveguides are controlled by embedding the nonlinear defect rods. We demonstrate that the electrice interaction in such waveguiding structures is nonlocal, and we suggest a novel theoretical approach, based on the e ective discrete equations, for describing both linear and nonlinear properties of such photoniccrystal waveguides and circuits, including the localized states at the waveguide bends. A dditionally, we study the transm ission of waveguide bends and emphasize the role of evanescent m odes for the correct analysis of their properties.

The paper is organized as follows. In Sec. 2, we introduce ourm odelofa two-dim ensional (2D) photonic crystal and provide a brief derivation of the e ective discrete equations for the photonic-crystalw avequides created by rem oved or em bedded rods, based on the G reen function technique. In Sec. 3, we apply these discrete equations for the analysis of the transmission of straight wavequides, including the resonant transmission through an array of nonlinear defect rods embedded into a straight wavequide. Additionally, we discuss a link between our approach and the results obtained in the fram ework of the fam iliar tight-binding approximation often used in the solid-state physics models, and emphasize the important role of the evanescent modes which can not be accounted for in the fram ework of the tight-binding approxim ation. Section 4 is devoted to the study of wavequide bends. First, we discuss the localized modes supported by a waveguide bend, and then we analyze the transm ission of the waveguide bends. W e dem onstrate that the waveguide bends with embedded nonlinear defects can be used for a very e ective control of light transm ission. Section 5 concludes the paper with a sum m ary of the results and further applications of our approach.

2. E ective discrete equations

In this Section, we suggest and describe a novel theoretical approach, based on the e ective discrete equations, for describing many of the properties of the photoniccrystal waveguides and circuits, including the transm ission spectra of sharp waveguide bends. This is an im portant part of our analysis because the properties of the photonic crystals and photonic crystal waveguides are usually studied by solving M axwell's equations num erically, and such calculations are, generally speaking, tim e consum ing. M oreover, the num erical solutions do not always provide a good physical insight. The e ective discrete equations we derive below and employ further in the paper are somewhat analogous to the Kirchho equations for the electric circuits. However, in contrast to electronics, in photonic crystals both di raction and interference become important, and thus the resulting equations involve the long-range interaction e ects.

W e introduce our approach for a simple model of 2D photonic crystals consisting of in nitely long dielectric rods arranged in the form of a square lattice with the lattice spacing a. W e study the light propagation in the plane norm alto the rods, assuming that the rods have a

radius $r_0 = 0.18a$ and the dielectric constant $"_0 = 11.56$ (this corresponds to G aA s or Siat the wavelength 1.55 m). For the electric eld E (x;t) = e^{i!t}E (x j!) polarized parallel to the rods, M axwell's equations reduce to the eigenvalue problem

$$r^{2} + \frac{!}{c}^{2} (x) E (x j!) = 0;$$
 (1)

which can be solved by the plane-wave method⁷. A perfect photonic crystal of this type possesses a large (38%) complete band gap between ! = 0.303 2 c=a and ! = 0.444 2 c=a (see Fig.1), and it has been extensively employed during last few years for the study of bound states⁸, transmission of light through sharp bends^{9;10}, waveguide branches¹¹ and intersections¹², channel drop lters¹³, nonlinear localized modes in straight waveguides⁵ and discrete spatial solitons in perfect 2D photonic crystals⁶. Recently, this type of photonic crystal with a 90° bent waveguide has been fabricated in macro-porous silicon with a = 0.57 m and a complete band gap at 1:55 m¹⁴.

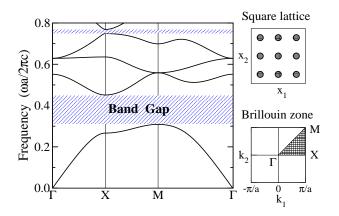


Fig. 1. The band-gap structure of the photonic crystal created by a square lattice of dielectric rods with $r_0 = 0.18a$ and $\mathbf{u}_0 = 11.56$; the band gaps are hatched. The top right inset shows a cross-sectional view of the 2D photonic crystal. The bottom right inset shows the corresponding B rillouin zone, with the irreducible zone shaded.

To create a waveguide circuit, we introduce a system of defects and assume, for simplicity, that the defects are identical rods of the radius $r_{\rm d}$ located at the points $x_{\rm n}$, where n is the index number of the defect rods. Im – portantly, the sim ilar approach can be employed equally well for the study of the defects created by removing isolated rods in a perfect 2D lattice, and we demonstrate such examples below .

In the photonic crystal with defects, the dielectric constant "(x) can be presented as a sum of the periodic and defect-induced term s, i.e. "(x) = " $_{p}(x)$ + "(x), with

$$"(x) = \int_{a}^{x} [E(x j!)]f(x x_{n}); \qquad (2)$$

where $f(\mathbf{x}) = 1$ for $\mathbf{\dot{x}j} < \mathbf{r}_d$, and it vanishes otherwise.

Equation (1) can be therefore written in the following integral form

$$E(x j!) = \frac{!}{c} d^{2}y G(x;y j!) "(y) E(y j!);$$
(3)

where G (x; y j!) is the G reen function of a perfect 2D photonic crystal (see, e.g., R ef. 5).

A single defect rod is described by the function $"(x) = "_d f(x)$, and it can support one orm ore localized m odes. Such localized m odes are the eigenm odes of the discrete spectrum of the following eigenvalue problem,

$$E_{1}(\mathbf{x}) = \frac{!_{1}}{c} \frac{2^{Z}}{r_{d}} d^{2}\mathbf{y} G(\mathbf{x};\mathbf{y};\mathbf{j}!_{1}) "_{d}f(\mathbf{y}) E_{1}(\mathbf{y});$$
(4)

where $!_1$ is the frequency (a discrete eigenvalue) of the l-th eigenm ode and $E_1(x)$ is the corresponding electric eld.

W hen we increase the number of defect rods (for example, in order to create photonic-crystal waveguide circuits⁹^{{13}}, the numerical solution of the integral equation (3) becomes complicated and, moreover, it is severely restricted by the current computer facilities. Therefore, one of our mapr goals in this paper is to develop a new approximate physical model that would allow the application of fast numerical techniques, combined with a reasonably good accuracy, for the study of more complicated (linear and nonlinear) waveguide circuits in photonic crystals.

To achieve our goal, we consider the localized states created by a (in general, complex) system of defects (2) as a linear combination of the localized modes $E_1(x)$ supported by isolated defects:

$$E(x j!) = \sum_{n}^{X} (1) (!) E_1(x x_n) :$$
(5)

Substituting Eq. (5) into Eq. (3), multiplying it by $E_{1^0}(\mathbf{x} \quad \mathbf{x}_{n^0})$ and integrating with \mathbf{x} , we obtain a system of discrete equations for the amplitudes $\binom{1}{n}$ of the l-th eigenmodes localized at n-th defect rods:

$$\begin{array}{cccc} X & & & X \\ & & & 1^{0} ; n^{0} & (1) \\ & & & 1_{fn} & n \end{array} & & \mathbf{T}_{d} & & \frac{1^{0} ; n^{0}}{1 ; n ; rm} & (!) & & n \end{array}$$

where

$$\begin{array}{l}
\overset{1^{0} pn^{0}}{l_{pn}} = & d^{2} \mathbf{x} \ E_{1} \left(\mathbf{x} \quad \mathbf{x}_{n} \right) E_{1^{0}} \left(\mathbf{x} \quad \mathbf{x}_{n^{0}} \right); \\
\overset{1^{0} pn^{0}}{l_{pn} m} \left(! \right) = & \frac{!}{c} \quad \overset{2^{Z}}{d^{2} \mathbf{x}} \ E_{1^{0}} \left(\mathbf{x} \quad \mathbf{x}_{n^{0}} \right) \\
\overset{2}{d^{2} \mathbf{y}} \ G \left(\mathbf{x}; \mathbf{y} \ \mathbf{j} ! \right) f \left(\mathbf{y} \quad \mathbf{x}_{m} \right) E_{1} \left(\mathbf{y} \quad \mathbf{x}_{n} \right); \quad (7)
\end{array}$$

It should be emphasized that the discrete equations (6) { (7) are derived by using only the approximation provided by the ansatz (5). As can be demonstrated by comparing the approximate results with the direct numerical solutions of the M axwell equations, this approximation is usually very accurate, and it can be used in many physical problem s.

However, the e ective discrete equations (6) are still too complicated and, in some cases, they can be simpli-

ed further still rem aining very accurate. A good example is the case of the photonic crystal waveguides created by a sequence of largely separated defect rods. Such waveguides are known as the coupled-resonator optical waveguides (CROW s)^{15;16} or coupled-cavity waveguides (CCW s)¹⁷. For those cases, the localized modes are located at each of the defect sites being only weakly coupled with the sim ilar neighboring modes. A s is known, such a situation can be described very accurately by the so-called tight-binding approximation (see also Ref. 18). For our form alism, this means that $\frac{1^{0}m^{0}}{1m} = \frac{1^{0}m^{0}}{1mm} = 0$ for jn^{0} n j> 1 and jn^{0} m j> 1. The most im portant feature of the CROW circuits is that their bends are re-

ectionless throughout the entire band^{5;17}. This is in a sharp contrast with the conventional photonic crystal waveguides created by a sequence of the rem oved or introduced defect rods (see e.g., Ref. 9 and references therein) where the 100% transm ission through a waveguide bend is known to occur only at certain resonant frequencies. In spite of this visible advantage, the CROW structures have a very narrow guiding band and, as a result, e ectively they demonstrate a complete transm ission through the waveguide bend in a narrow frequency interval too.

Below, we consider di erent types of photonic crystal waveguides and show that a very accurate simpli cation of Eqs. (6) is provided by accounting for an indirect coupling between the rem ote defect m odes, caused by the slowly decaying G reen function, $\frac{1^0 r^0}{lrn r^m} \notin 0$ for 'n0 ni L, where the number L of e ectively coupled defects lies usually between ve and ten. As we show below, this type of interaction, which is neglected in the tight-binding approxim ation, is in portant for understanding the transmission properties of the photoniccrystalwavequides. At the same time, we neglect a direct overlap between the nearest-neighbor eigenm odes, which is often considered to be im portant^{15;17}), i.e. we consider $l_{jn}^{0} = l_{j10} n_{jn}^{n}$ (with l_{j10} being the D irac delta function) and $\frac{1^{0}m^{0}}{1mm} = 0$ for $n \in m$. Taking into account this interaction leads to negligible corrections only.

A ssum ing that the defects support only the monopole eigenmodes (marked by l = 1), the coeccients (7) can be calculated reasonably accurately in approximation that the electric eld remains constant inside the defect rods, i.e. $E_1(x) = f(x)$. This corresponds to the averaging of the electric eld in the integral equation (3) over the cross-section of the defect rods^{19,5}. In this case the re-

sulting approxim ate discrete equation for the amplitudes of the electric elds E_n (!) $\frac{1}{n}$ (!) of the eigenmodes excited at the defect sites has the following matrix form:

$$M_{n,m} (!) E_{m} (!) = 0;$$

$$M_{n,m} (!) = {}^{m} d(E_{m}) J_{n,m} (!) _{n,m}; \qquad (8)$$

where $J_{n,m}$ (!) $\int_{1,m,m}^{1,m} (!)$ is a coupling constant calculated in the approximation that $E_1(x)$ f(x), so that

$$J_{n,m} (!) = \frac{!}{c} \int_{r_d}^{2} d^2 y G(\mathbf{x}_n; \mathbf{x}_m + y j!)$$
(9)

is completely determ ined by the G reen function of a perfect 2D photonic crystal (see details in R efs. 5,6).

First of all, we check the accuracy of our approximate model (8) for the case of a single defect located at the point \mathbf{x}_0 . In this case, Eq. (8) yields the simple result $J_{0;0}(!_d) = 1 = "_d$, and this expression deness the frequency $!_d$ of the defect mode. In particular, applying this result to the case when the defect is created by a single removed rod, we obtain the frequency $!_d = 0.391$ 2 c=a which di ers only by 1% from the value $!_d = 0.387$ 2 c=a calculated with the help of the M IT Photonic-Bands num erical code⁷.

3. Straight waveguides

A.W aveguide dispersion

A simple single-mode waveguide can be created by removing a row of rods (see the inset in Fig. 2). A ssum ing that the waveguide is straight ($M_{n,m} = M_n = 0$) and neglecting the coupling between the remote defect rods (i.e. $M_n = 0$ for all jn m j> L), we rewrite Eq. (8) in the transferm atrix form, $F_{n+1} = \hat{T}F_n$, where we introduce the vector $F_n = fE_n; E_n = 1; :::; E_n = 2L+1$ g and the transferm atrix $\hat{T} = fT_{i,j}$ with the non-zero elements

$$T_{1;j}(!) = \frac{M_{L j}(!)}{M_{L}(!)} \text{ for } j = 1;2; ...; 2L ;$$

$$T_{j;j+1} = 1 \text{ for } j = 1;2; ...; 2L 1 :$$
(10)

Solving the eigenvalue problem

$$\hat{T}(!)^{p} = \exp fik_{p}(!)g^{p};$$
 (11)

we can d the 2L eigenmodes of the photonic-crystal waveguide. The eigenmodes with real wavenumbers k_p (!) correspond to the modes propagating along the waveguide. In the waveguide shown in Fig. 2, there exist only two such modes (we denote them as $^{-1}$ and $^{-2}$), propagating in the opposite directions ($k_1 = k_2 > 0$).

In Fig. 2 we plot the dispersion relation k_1 (!) calculated by three di erent methods: nst (solid curve) is calculated directly by the super-cellmethod⁷, and other two are found from Eq. (11) in the nearest-neighbor approximation (L=1, dotted curve) corresponding to the tight-binding models, and also by taking into account the long-range interaction through the coupling between several neighbors (L=7, dashed curve). Indeed, we observe a very good agreement for the conditions when the long-range interaction is taken into account.

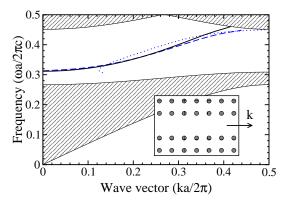


Fig. 2. D ispersion relation for a 2D photonic-crystal waveguide (shown in the inset) calculated by the super-cellm ethod⁷ (solid), and from the approxim at equations (10) { (11) for L = 7 (dashed) and L = 1 (dotted). The hatched areas are the projected band structure of a perfect 2D crystal.

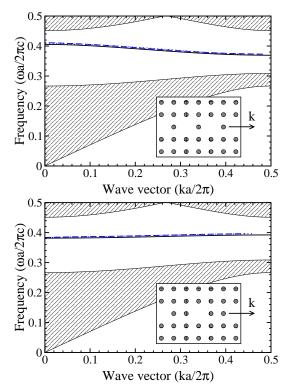


Fig. 3. The same as in Fig. 2 but for two other types of waveguides better described by the tight-binding models.

It is in portant to com pare the results provided by our m ethod with those obtained in the tight-binding approximation. For the waveguide shown in Fig. 2, such an approximation, rigorously speaking, is not valid, but its analog can be considered at least form ally for the case of the nearest-neighbor interaction when in Eqs. (10) { (11)we take L=1. The interaction between the rem ote rods cannot be neglected as soon as we study the waveguides created by rem oving (or inserting) all rods along the row or more complicated structures of this type. In such a case, as is seen from Fig.2, the dispersion relation found in the tight-binding approximation is incorrect and, in order to obtain accurate results, one should take into account the coupling between several defect rods. We verify that this statem ent is also valid for multim ode waveguides, e.g. those created by rem oving several rows of rods.

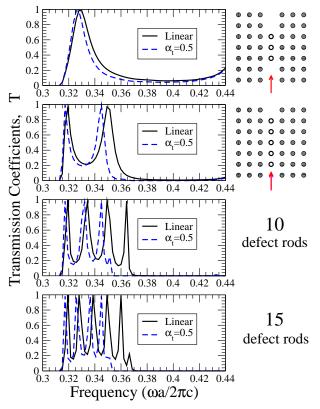


Fig.4. Transm ission coe cients of an array of nonlinear defect rods calculated from Eqs. (8) { (13) with L = 7 in the linear lim it of very sm all j $_{\rm t}$ $_{\rm f}^2$ (solid curves) and for the nonlinear transm ission when the output intensity is j $_{\rm t}$ $_{\rm f}^2$ = 0.25 (dashed curves), for di erent num bers of the defects. We use nonlinear defect rods with the dielectric constant ${}^{(0)}_{\rm d}$ = 7; they are marked by open circles on the right insets.

However, for the waveguides of a di erent geom etry, when only the second (or third, etc) rods are rem oved, all m ethods provide a reasonably good agreem ent with the direct num erical results, as is shown for two exam ples in Fig. 3. In this case, the waveguides are created by an array of cavity modes, and they are sin ilar to the CROW structures earlier analyzed by several authors^{15{17}. Thus, the dispersion properties of CROW s (or sim ilar waveguides) can be described with a good accuracy by the tight-binding approximation; our new approach con m s this conclusion, and it provides a simple m ethod for the derivation of the approximate equations.

B.Resonant transm ission of an array of defects

In addition to the propagating guided m odes, in photonic crystal waveguides there always exist evanescent m odes with in aginary k_p . These modes cannot be accounted for in the fram ework of the tight-binding theory that relies on the nearest-neighbor interaction between the defect rods. A lthough the evanescent modes remain som ew hat hidden" in straight waveguides, they become crucially important in more elaborated structures such as waveguides with embedded linear or nonlinear defects, waveguide bends and branches. In these cases the evanescent modes manifest them selves in several di erent ways. In particular, they determ ine non-trivial transmission properties of the photonic-crystal circuits considered below.

As the rst example of the application of our approach, we study the transm ission of a straight waveguide with embedded nonlinear defects. Such a structure can be considered as two sem i-in nite straight waveguides coupled by a nite region of defects located between them. The coupling region may include both linear (as a domain of a perfect wavequide) and nonlinear (embedded) defects. W e assume that the defect rods inside the coupling region are characterized by the index that runs from a to b, and the amplitudes E_m (m = a;:::;b) of the electric eld at the defects are all unknown.We num ber the guided modes (11) in the following way: p = 1corresponds to the mode propagating in the direction of the nonlinear section (for both ends of the waveguide), p = 2 corresponds to the mode, propagating in the opposite direction, $p = 3; \dots; L + 1$ correspond to the evanescent modes which grow in the direction of the nonlinear section, and p = L + 2; :::; 2L correspond to the evanescent modes which decay in the direction of the nonlinear section. Then, we can write the incom ing and outgoing waves in the sem i-in nite waveguide sections as a superposition of the guided modes:

$$E_{m}^{in} = \frac{1}{iam} + \frac{2}{ram} + \frac{im}{pam}; \quad (12)$$

form = a 2L;::;a 1, and

$$E_{m}^{out} = {}_{t \ m \ b}^{2} + {}_{p \ m \ b}^{out \ p}; \qquad (13)$$

form = b+1;:::;b+2L, where p = and p = are unknown amplitudes of the evanescent modes growing in the direction of the nonlinear section, whereas i, t and r are unknown am plitudes of the incoming, transmitted, and rejected propagating waves. We take into account that the evanescent modes with p > L + 1 (growing in the direction of waveguide ends) must vanish. Now, substituting Eqs. (12) { (13) into Eq. (8), we obtain a system of linear (or nonlinear, for nonlinear defects) equations with 2L + b a + 1 unknown. Solving this system, we ind the transmission coeccient, $T = j_t = i f$, and rejection coeccient, $R = j_r = i f$, as functions of the light frequency, !, and intensity, $j_i f$ or $j_t f$. Recently, we have dem onstrated²⁰ that the linear transmission properties of the waveguide bends are described very accurately by this approach. Below, we study nonlinear transmission of the photonic-crystal waveguides and waveguide bends.

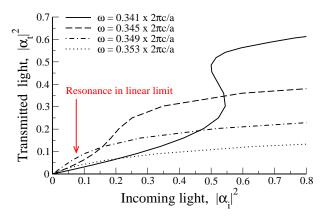


Fig. 5. Bistability in the nonlinear transmission of an array of ve nonlinear defect rods shown in Fig. 4(b).

In Fig. 4, we present our results for the transm ission spectra of the straight waveguides (created by a row of rem oved rods) with an array of embedded nonlinear defects. We assume throughout the paper that all non-linear defect rods are identical, with the radius $r_d = r_0 = 0.18a$ and the dielectric constant, $\mathbf{u}_d = \mathbf{u}_d^{(0)} + \mathbf{E}_n \mathbf{\hat{f}}$ (with $\mathbf{u}_d^{(0)} = 7$), which grows linearly with the light intensity (the so-called Kerre ect). In the linear limit, the embedded defects behave like an electric resonant

Iter, and only the waves with some speci c resonance frequencies can be e ectively transmitted through the defect section. The resonances appear due to the excitation of cavity modes inside the defect region, whereas a single defect does not demonstrate any resonant behavior. When the intensity of the input wave grows, the resonant frequencies found in the linear limit get shifted to lower values. The sensitivity of di erent resonances to the change of the light intensity is quite di erent and m ay be tuned by m atching of the defect param eters. The nonlinear resonant transmission is found to possess bistability, similar to another problem of the nonlinear transmission (see, e.g., R efs. 21). The bistable transmission occurs for the frequencies smaller then the resonant, in a linear limit, frequency (see Fig. 5).

C.An optical diode

An all-optical \diode" is a spatially nonreciprocal device which allows unidirectional propagation of a signal at a given wavelength. In the ideal case, the diode transm ission is 100% in the \forward" propagation, while it is much smaller or vanishes for \backward" (opposite) propagation, yielding a unitary contrast.

The rst study of the operational mechanism for a passive optical diode based on a photonic band gap material was carried out by Scalora et al.^{22;23}. These authors considered the pulse propagation near the band edge of a one-dimensional photonic crystal structure with a spatial gradiation in the linear refractive index, together with a nonlinear medium response, and found that such a structure can result in unidirectional pulse propagation.

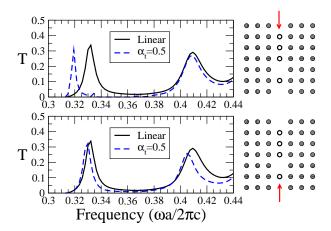


Fig.6. Transm ission coe cients of an asym m etric array of nonlinear defect rods calculated for the sam e param eters as in Fig.4.

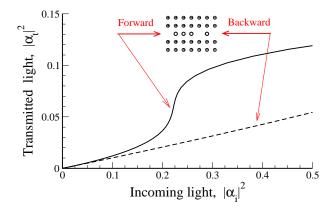


Fig. 7. Nonlinear transmission of the optical diode for the forward (see top of Fig. 6) and backward (see bottom of Fig. 6) directions at the light frequency $! = 0.326 \quad 2 \quad c=a$.

To implement this concept for the waveguide geometry discussed above, we consider the asymmetric structure made of four nonlinear defect rods, as shown in the right insets on Fig. 6. Figure 6 shows the transmission spectra

of such an asymmetric structure in the opposite directions indicated by two arrows in the right insets. As is seen, in the linear lim it the transmission is characterized by two resonant frequencies and does not depend on the propagation direction. However, since the sensitivity of both resonant frequencies to the change of the light intensity is di erent for the \forward" (see Fig. 6, top) and \backward" (see Fig. 6, bottom) propagation directions, the transmission becomes, in the vicinity of resonant frequencies, highly asymmetric for large input intensities. This results into nearly unidirectional waveguide transmission, as shown in Fig. 7.

In contrast to the perfect resonators used in F ig. 4, the transm ission of the asymmetric structure under consideration is not very e cient at the resonant frequencies. However, we believe that the optical diode e ect, with much better e ciency, can be found in other types of the waveguide geometry and a unitary contrast can be achieved by a proper optimization of the waveguide and defect parameters, that can be carried out by employing our method and the e ective discrete equations derived above.

4. W aveguide bends

In addition to the non-trivial transmission properties, the evanescent m odes m anifest them selves in creation of localized bound states in the vicinity of the wavequide bends or branches. To dem onstrate this e ect, we consider the simplest case of a sharp bend of the waveguide created by a row of removed rods. As was shown in Ref. 8, in the cases when the waveguide bend can be considered as a nite section of a waveguide of di erent type, the bound states correspond closely to cavity modes excited in this nite section. How ever, such a sim pli ed one-dim ensionalm odeldoes not describe correctly m ore complicated cases^{β}, even the properties of the bent waveguide depicted in Fig. 8. The situation becomes even m ore com plicated for the waveguide branches¹¹. In contrast, solving the discrete equations (8) we can nd the frequencies and pro les of the bound states excited in an arbitrary complex set of defects. For particular case of the wavequide bend shown in Fig. 8, we nd two bound states localized at the bend and their pro les (cf. our Fig. 8 with Fig. 9 in Ref. 8). It should be noted that the frequencies of the modes are found from Eq. (8) with the accuracy of 1:5% .

A dditionally, the evanescent modes determine the non-trivial transmission properties of the waveguide bends which can also be calculated with the help of our discrete equations. To demonstrate these features, we consider a bent waveguide consisting of two coupled sem i-in nite straight waveguides with a nite section of defects between them. The nite section includes a bend with a safety margin of the straight waveguide at both ends.

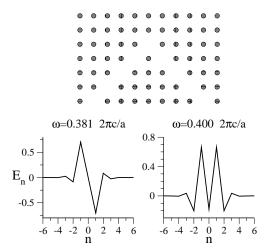


Fig.8. Electric eld E_n for two bound states supported by a 90° waveguide bend shown in the top. Center of the bend is located at n = 0.

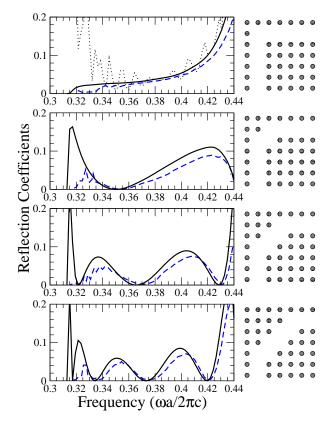


Fig. 9. Relection coelecters calculated by the nite-dilerence time-domain method (dashed, from Ref. 9) and from Eqs. (8){(13) with L = 7 (full lines) and L = 2(dotted, only in the top plot), for dilerent bend geometries.

Similar to what we discussed in Sec. 3B for the straight waveguides, we solve the system of e ective discrete equations to nd the transmission, $T = j_t = i\hat{f}$, and re ection, $R = j_r = i\hat{f}$, coe cients of the waveguide bends. In Fig. 9 we present our results for the transmission spectra of several types of bent waveguides,

which have been discussed in R ef. 9, where the possibility of high transm ission through sharp bends in photoniccrystal waveguides was not demonstrated. We com – pare the rejection coe cients calculated by the nitedi erence time-dom ain method in R ef. 9 (dashed lines) with our results, calculated from Eqs. (8) { (13) for L = 7(full lines) and for L = 2 (dotted line in the top plot). As is clearly seen, Eqs. (8) { (13) provide a very accurate method for calculating the transmission spectra of the waveguide bends, if only we account for long-range interactions. It should be emphasized that the approximation, in which the only next-neighbor interactions are taken in to account, is usually too crude, while the tightbinding theory incorrectly predicts a perfect transm ission for all guiding frequencies.

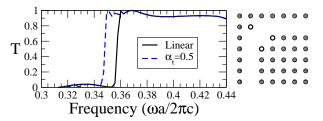


Fig. 10. Transm ission of a waveguide bend with three embedded nonlinear defect rods in the linear (solid curve) and nonlinear (dashed curve) regimes. Defect rods have the dielectric constant $\mathbf{u}_{d}^{(0)} = 7$, and they are marked by open circles.

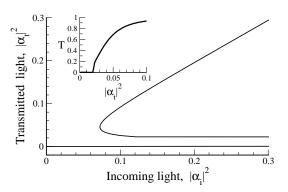


Fig. 11. Bistable nonlinear transmission through the waveguide bend shown in Fig. 10, for the light frequency $! = 0.351 \quad 2 \text{ c=a}$.

The resonant transm ission can be modi ed dram atically by introducing both linear and/or nonlinear defects into the waveguide bends. To illustrate such features, we consider the waveguide bend with three em – bedded nonlinear defects, as is depicted in Fig. 10 on the right inset, where these defects are shown by open circles. In the linear regim e, such a sharp bend behaves as an optical threshold device that e ciently transm its the guided waves with frequencies above the threshold one, but completely re ects the waves with the lower frequencies. The transm ission coe cient of this waveguide bend in the linear lim it is shown in Fig.10 by a solid curve. W hen the input intensity increases, the threshold frequency decreases, extending the transm ission region (see a dashed curve in Fig. 10). The resulting transm ission as a function of the input intensity dem onstrates a sharp nonlinear threshold character with an extrem ely low transm ission of the waves below a certain (rather sm all) threshold intensity, see Fig. 11.

5. C on clusions

W e have suggested a novel theoretical approach for describing a broad range of transm ission properties of the photonic crystal waveguides and circuits. Our approach is based on the analysis of the e ective discrete equations derived with the help of the G reen function technique, and it generalizes the fam iliar tight-binding approxim ations usually employed to study the coupled-resonator or coupled-cavity optical waveguides. The e ective discrete equations we have introduced in this paper emphasize the important role played by the evanescent modes in the transmission characteristics of the photonic crystal circuits with waveguide bends and/or em bedded defects. Employing this technique, we have studied the properties of several in portant elem ents of the (linear and nonlinear) photonic crystal circuits, including a nonlinear bistable transmitter and an optical diode created by an asymmetric structure of nonlinear defects. We believe that our approach can be useful for solving more com plicated problems, and it can be applied to study the transm ission characteristics of the waveguide branches, channeldrop lters, etc.

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